

**Supplementary Document of Perovskites for Solar Thermoelectric  
Applications: a First Principle Study of  $\text{CH}_3\text{NH}_3\text{AI}_3$  (A=Pb and Sn)**

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Table SI: Ab initio optimized lattice constants a, b and c (Å) (see Fig. 1a) of the pseudo-cubic MAPbI<sub>3</sub> with MA along the <100>, <110> and <111> directions, and those of pseudo-cubic MASnI<sub>3</sub> with MA along the <100> direction. The term AVE represents the average value over three lattice constants. The displacement of the metal Pb ion of MAPbI<sub>3</sub> in each of the three cases is shown in Fig. S1.

Lattice Constant	MAPbI <sub>3</sub>			MASnI <sub>3</sub>
	MA100	MA110	MA111	MA100
a	6.4504	6.4271	6.4113	6.3535
b	6.3810	6.4470	6.4192	6.3384
c	6.4601	6.3373	6.4132	6.3641
AVE.	6.4305	6.4038	6.4145	6.3520

Table SII: Calculated longitudinal ( $m_{\parallel}^*$ ), transverse ( $m_{\perp}^*$ ), conductivity ( $m_l^*$ ), band ( $m_b^*$ ), and density of state effective mass ( $m^*$ ) of electrons ( $e^-$ ) and holes ( $h^+$ ) at two splitted conduction edges (LUMO1 and LUMO2) and two splitted valence band edges (HOMO1 and HOMO2) at the R point in the Brillouin Zone (see Fig. 2a and 3a). All effective masses are in units of the electron mass ( $m_e$ ). The term AVE represents the averaged value over the two splitted bands. All results were obtained with DFT-PBE calculations. The effective mass  $m^*$  was obtained by summing over two bands and it is indicated by the bold figures.

	MAPbI <sub>3</sub> ( $e^-$ )			MAPbI <sub>3</sub> ( $h^+$ )			MASnI <sub>3</sub> ( $e^-$ )			MASnI <sub>3</sub> ( $h^+$ )		
	LUMO1	LUMO2	AVE.	HOMO1	HOMO2	AVE.	LUMO1	LUMO2	AVE.	HOMO1	HOMO2	AVE.
$m_{\parallel}^*$	0.2527	0.1282	0.1905	0.3435	0.3366	0.3398	0.2825	0.3021	0.2923	0.1872	0.1711	0.1792
$m_{\perp}^*$	0.0853	0.0750	0.0802	0.1012	0.0855	0.0934	0.0935	0.0868	0.0902	0.0887	0.0857	0.0872
$m_l^*$	0.1095	0.0870	0.0983	0.1323	0.1138	0.1231	0.1203	0.1138	0.1171	0.1076	0.1028	0.1052
$m_b^*$	0.1227	0.0897	0.1062	0.1521	0.1350	0.1436	0.1352	0.1315	0.1334	0.1138	0.1079	0.1109
$m^*$	0.1227	0.0897	<b>0.2124</b>	0.1521	0.1350	<b>0.2871</b>	0.1352	0.1315	<b>0.2668</b>	0.1138	0.1079	<b>0.2217</b>

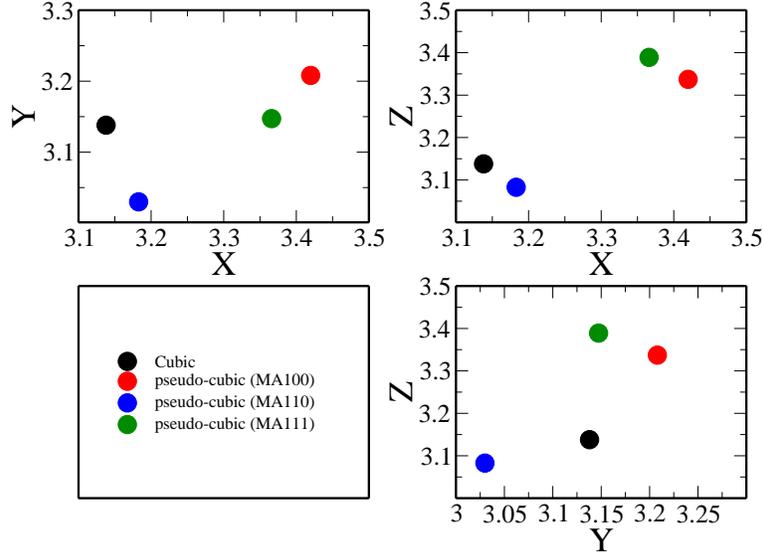


Figure S1: Positions of Pb atoms in MAPbI<sub>3</sub> samples for the perfect cubic structure (black), pseudo-cubic with MA along  $\langle 100 \rangle$  (red), pseudo-cubic with MA along  $\langle 110 \rangle$  (blue) and pseudo-cubic with MA along  $\langle 111 \rangle$  (green) direction, respectively.

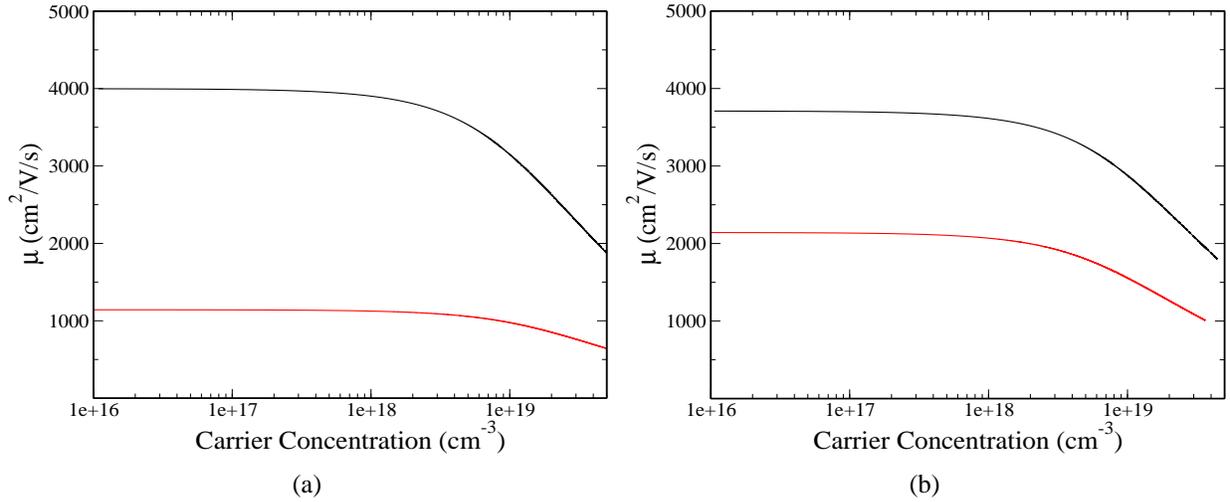


Figure S2: Calculated electron (black) and hole (red) mobilities ( $\mu$ ) as a function of carrier concentration at 400 K in pseudo-cubic CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> (a) and at 300 K in pseudo-cubic CH<sub>3</sub>NH<sub>3</sub>SnI<sub>3</sub> (b), by using the Kane model with  $G_0W_0$  band gaps and DFT-PBE effective masses.

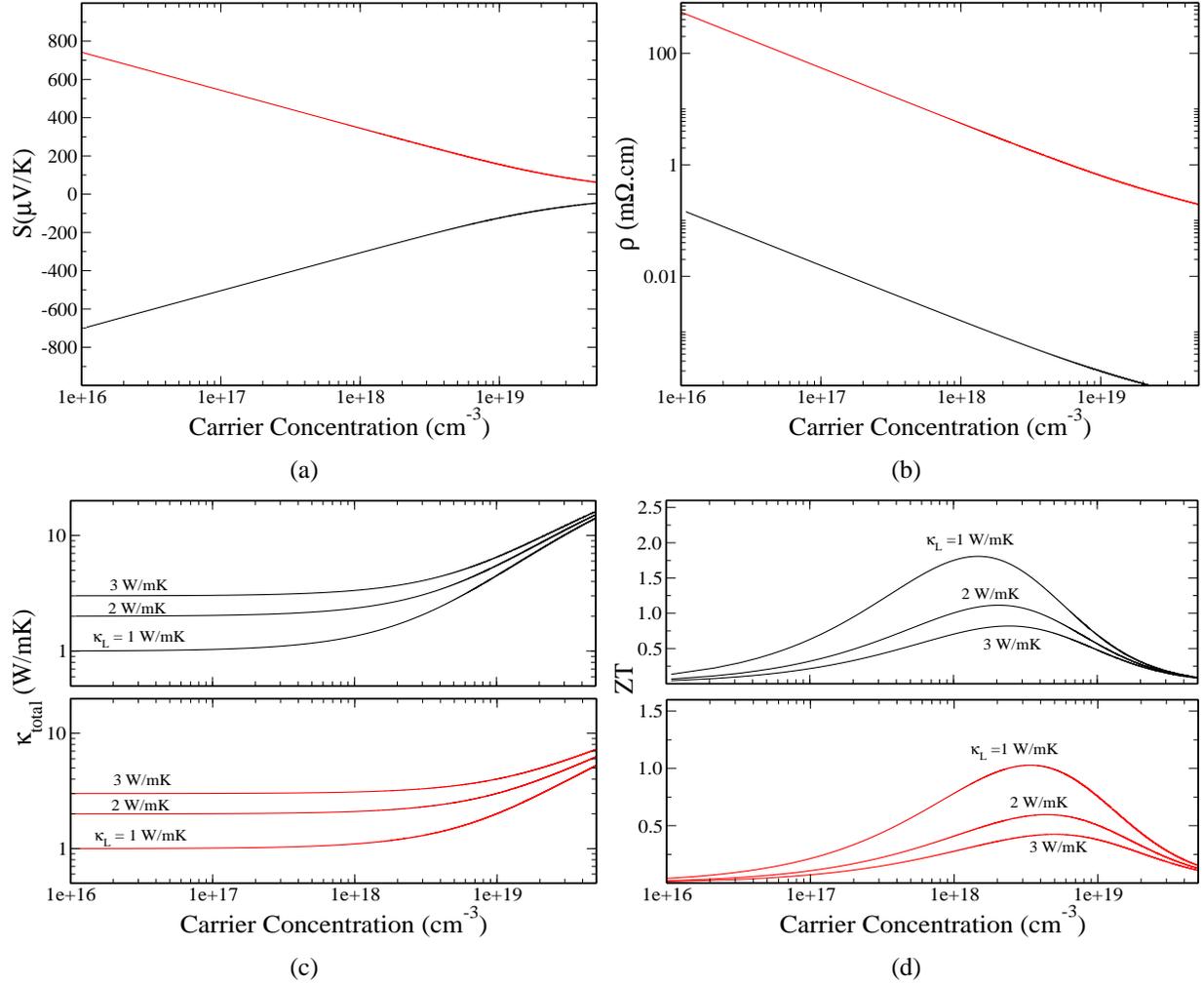


Figure S3: (a) Seebeck coefficients ( $S$ ), (b) electrical resistivities ( $\rho$ ), (c) total thermal conductivities ( $\kappa_{total}$ ), and (d) the predicted values of the material figure of merit ( $ZT$ ) as a function of carrier concentration with  $\kappa_L = 1, 2$  and  $3$  W/mK, at  $400$  K for n-type (black) and p-type (red) doped, pseudo-cubic  $\text{CH}_3\text{NH}_3\text{PbI}_3$ , obtained from the Kane model with  $G_0W_0$  band gaps and DFT-PBE effective masses. At the carrier concentration for which  $ZT$  is maximum,  $\kappa_e$  varies between  $0.45$  and  $0.75$  W/mK for n-type, and between  $0.30$  and  $0.43$  W/mK for p-type.

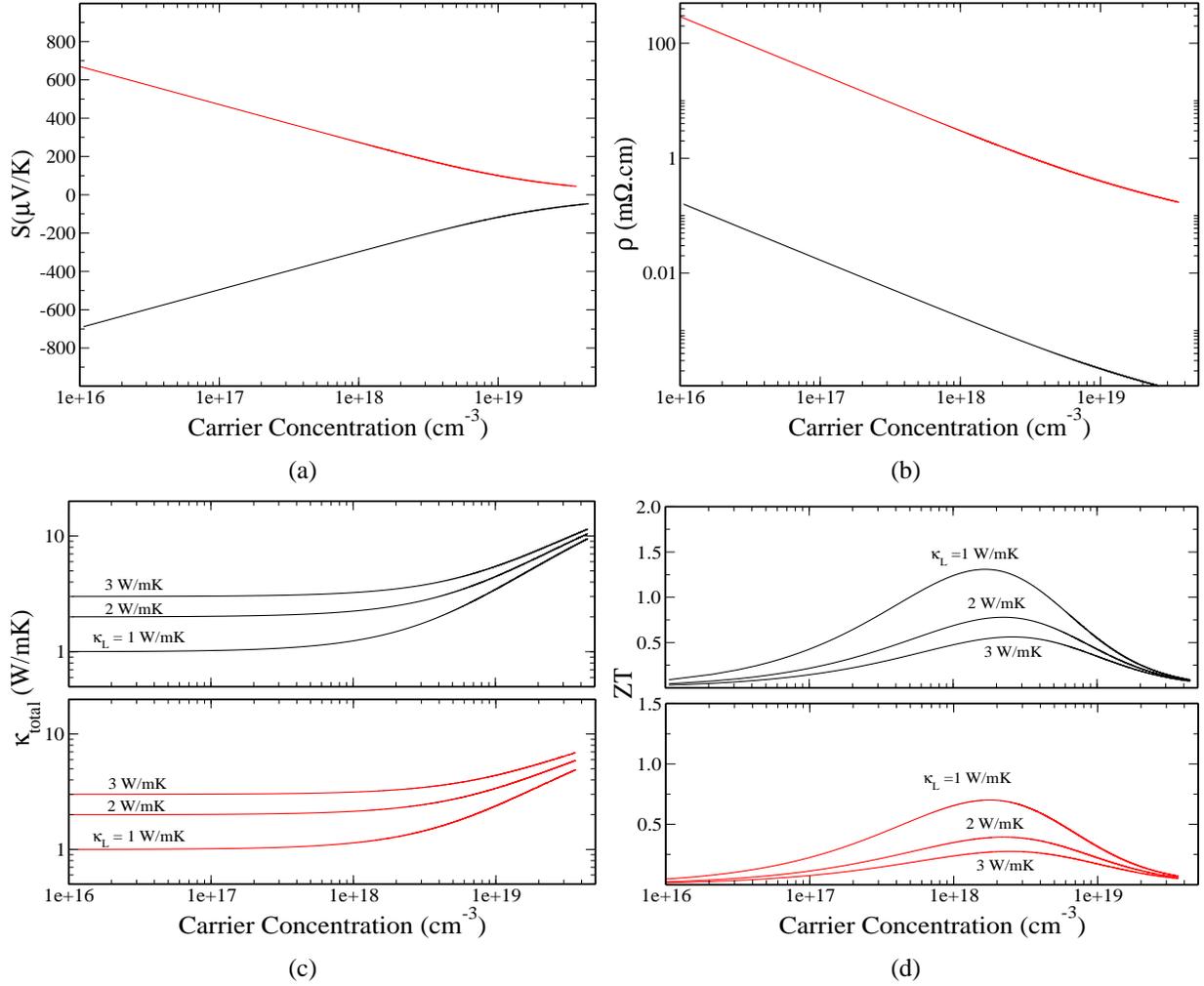


Figure S4: (a) Seebeck coefficients ( $S$ ), (b) electrical resistivities ( $\rho$ ), (c) total thermal conductivities ( $\kappa_{total}$ ), and (d) the predicted values of the material figure of merit ( $ZT$ ) as a function of carrier concentration with  $\kappa_L = 1, 2$  and  $3$  W/mK, at  $300$  K for n-type (black) and p-type (red) doped, pseudo-cubic  $\text{CH}_3\text{NH}_3\text{SnI}_3$ , obtained from the Kane model with  $G_0W_0$  band gaps and DFT-PBE effective masses. At the carrier concentration for which  $ZT$  is maximum,  $\kappa_e$  varies between  $0.38$  and  $0.62$  W/mK for n-type, and between  $0.24$  and  $0.31$  W/mK for p-type.